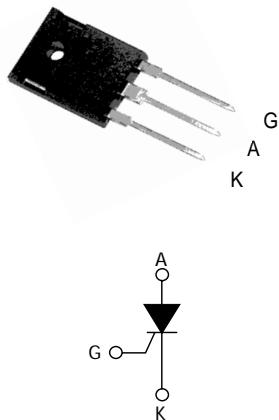
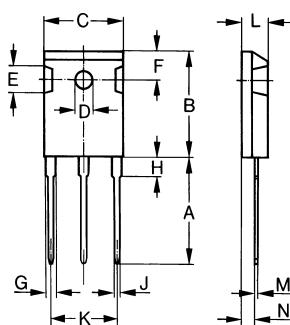


STYN255 thru STYN855

Discrete Thyristors(SCRs)



Dimensions TO-247AD



Dim.	Millimeter Min. Max.		Inches Min. Max.	
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value		Unit
$I_T(\text{RMS})$	RMS on-state current (180° conduction angle)		$T_c = 75^\circ\text{C}$	55	A
$I_T(\text{AV})$	Average on-state current (180° conduction angle)		$T_c = 75^\circ\text{C}$	35	A
I_{TSM}	Non repetitive surge peak on-state current	$tp = 8.3 \text{ ms}$	$T_j = 25^\circ\text{C}$	610	A
		$tp = 10 \text{ ms}$		580	
I^2t	I^2t Value for fusing		$T_j = 25^\circ\text{C}$	1680	A^2s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $tr < 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$tp = 20 \mu\text{s}$	$T_j = 125^\circ\text{C}$	8	A
$P_{G(\text{AV})}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	
				°C	
V_{RGM}	Maximum peak reverse gate voltage (for TN8 & TYN only)		5		V

STYN255 thru STYN855

Discrete Thyristors(SCRs)

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			TYNx08(S)	Unit
I_{GT}	$V_D = 12 \text{ V}$ $R_L = 33 \text{ W}$	MIN.	8	mA	
V_{GT}		MAX.	80		
V_{GD}		MAX.	1.3	V	
I_H	$I_T = 500 \text{ mA}$ Gate open	MAX.	150	mA	
I_L	$I_G = 1.2 I_{GT}$	MAX.	200	mA	
dV/dt	$V_D = 67 \% V_{DRM}$ Gate open	$T_j = 125^\circ\text{C}$	MIN.	1000	$\text{V}/\mu\text{s}$
V_{TM}	$I_{TM} = 100 \text{ A}$ $t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.9	V
V_{t0}	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	1.0	V
R_d	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	8.5	mW
I_{DRM}	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	10	μA
I_{RRM}		$T_j = 125^\circ\text{C}$		5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	0.9	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient (DC)	50	$^\circ\text{C/W}$

S= copper surface under tab

PRODUCT SELECTOR

Part Number	Voltage (xxx)	Sensitivity	Package
STYNx55	200~800	80 mA	TO-247AD

OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing mode
STYN x55	STYN x55	4.5 g	120	Bulk

Note: x = voltage